

## 1732 (H) x 1172 (V) Pixel

## Full-Frame CCD Color Image Sensor

## **Performance Specification**

Eastman Kodak Company

**Image Sensor Solutions** 

Rochester, New York 14650-2010

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## APPENDIX

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High Output Sensitivity (12 mV/e<sup>-</sup>)

1732 (H) x 1172 (V) Photosensitive Pixels

22.5mm (H) x 15.2mm (V) Photosensitive Area

• Low Dark Current (< 10pA/cm<sup>2</sup> @ 25°C)

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Features

2M Pixel Color Area CCD

2-Phase Register Clocking

**Enhanced Responsivity** 

**High Fill Factor (72%)** 

**Antiblooming Protection** 

13mm (H) x 13mm (V) Pixel Size

#### 1.2 Description

The KAF-2001CE is a high performance color area CCD (charge-coupled device) image sensor with 1732H x 1172V photoactive pixels designed for a wide range of color image sensing applications including digital imaging. Each pixel contains antiblooming protection by means of a lateral overflow drain thereby preventing image corruption during high light level conditions. Each of the 13 $\mu$ m square pixels are selectively covered with red, green or blue filters for color separation. The photoactive pixels are surrounded by a border of buffer and light-shielded pixels as shown in Figure 1. Total chip size is 24.3mm x 16.3mm and is housed in a 26-pin, 0.88" wide DIL ceramic package with 0.1" pin spacing.



Figure 1 - Functional Block Diagram



### **1.3** Image Acquisition

An electronic representation of an image is formed when incident photons falling on the sensor plane create electron-hole pairs within the device. These photon induced electrons are collected locally by the formation of potential wells at each photogate or pixel site. The number of electrons collected is linearly dependent on light level and exposure time and nonlinearly dependent on wavelength. When the pixel's capacity is reached, excess electrons are discharged into the lateral overflow drain to prevent crosstalk or 'blooming'. During the integration period, the  $\phi$ V1 and  $\phi$ V2 register clocks are held at a constant (low) level. See Figure 5. - Timing Diagrams.

### **1.4 Charge Transport**

Referring again to Figure 5 - Timing Diagrams, the integrated charge from each photogate is transported to the output using a two step process. Each line (row) of charge is first transported from the vertical CCD's to a horizontal CCD register using the  $\phi$ V1 and  $\phi$ V2 register clocks. The horizontal CCD is presented a new line on the rising edge of  $\phi$ V2 while  $\phi$ H1 is held high. At the start of frame readout, the  $\phi$ V2 clock must be pulsed once prior to normal line clocking. The horizontal CCD's then transport each line, pixel by pixel, to the output structure by alternately clocking the  $\phi$ H1 and  $\phi$ H2 pins in a complementary fashion. On each falling edge of  $\phi$ H2

### 1.5 Output Structure

Charge presented to the floating diffusion (FD) is converted into a voltage and current amplified in order to drive off-chip loads. The resulting voltage change seen at the output is linearly related to the amount of charge placed on FD. Once the signal has been sampled by the system electronics, the reset gate ( $\phi$ R) is clocked to remove the signal and FD is reset to the potential applied by RD. More signal at the floating diffusion reduces the voltage seen at the output pin. In order to activate the output structure, an off-chip load must be added to the Vout pin of the device - see Figure 4.

## 1.6 Dark Reference Pixels

Surrounding the peripheral of the device is a border of light shielded pixels. This includes 20 leading and 6 trailing pixels on every line excluding dummy pixels. There are also 20 full dark lines at the start of every frame and 4 full dark lines at the end of each frame. Under normal circumstances, these pixels do not respond to light. However, dark reference pixels in close proximity to an active pixel, or the outer bounds of the chip (including the first two lines out), can scavenge signal depending on light intensity and wavelength.

## **1.7** Active Buffer Pixels

The first 10 pixels in from any dark reference regions are classified as active buffer pixels. These pixels are light sensitive but tend to have inconsistent spectral responsivities than the remainder of the array. Active buffer pixels are not tested for defects and nonuniformities.

## 1.8 Dummy Pixels

Within the horizontal shift register are 12 leading and 2 trailing additional shift phases that are not associated with a column of pixels within the vertical register. These pixels contain only horizontal shift register dark current signal and do not respond to light. A few leading dummy pixels may scavenge false signal depending on operating conditions.



## 2.1 Package Drawing







Eastman Kodak Company – Image Sensor Solutions - Rochester, NY 14650-2010 Phone (716) 722-4385 Web: www.kodak.com/go/ccd Fax (716) 477-4947 E-mail: ccd@kodak.com

## 2.2 Pin Description

Pin	Symbol	Description	Pin	Symbol	Description
1, 6, 11, 12, 13	Vsub	Substrate (Ground)	14, 15, 26	Vsub	Substrate (Ground)
2	Vout	Video Output	16, 17	φV1	Vertical CCD Clock - Phase 1
3	Vss	Amplifier Supply Return	18, 19	φV2	Vertical CCD Clock - Phase 2
4	Vrd	Reset Drain	20, 21	φV2	Vertical CCD Clock - Phase 2
5	φR	Reset Clock	22, 3	φV1	Vertical CCD Clock - Phase 1
7	OG	Output Gate	24	LOD/Guard	Lateral Overflow Drain/Guard Ring
8	φH1	Horizontal CCD Clock - Phase 1	25	Vdd	Amplifier Supply
9	<b></b> ФН2	Horizontal CCD Clock - Phase 2			
10	LOD/Guard	Lateral Overflow Drain/Guard Ring			



Figure 3 - Package Pin Designations



## 3.1 Absolute Maximum Ratings

Description	Symbol	Min.	Max.	Units	Notes
Diode Pin Voltages	Vdiode	0	16	V	1, 2
Gate Pin Voltages - Type 1	Valode Vgate1	-10	10	V	1, 2
Gate Pin Voltages - Type 2	Vgate2	0	10	V	1, 4
Inter-Gate Voltages	Vg-g		10	V	5
φV2-φH1 Voltages	V <sub>V-H</sub>		17	V	6
φV1, φV2 - LOD Voltages	V <sub>V-L</sub>		20	V	7
Output Bias Current	Iout		-10	mA	8
Output Load Capacitance	Cload		15	pF	8
Temperature	Т	0	70	°C	9
Humidity	RH	5	90	%	10

#### Notes:

- 1. Referenced to pin Vsub.
- 2. Includes pins: Vrd, Vdd, Vss, Vout, LOD/Guard.
- 3. Includes pins:  $\phi$ V1,  $\phi$ V2,  $\phi$ H1,  $\phi$ H2.
- 4. Includes pins with ESD protection:  $\phi$ R, OG.
- 5. Voltage difference between overlapping gates. Includes:  $\phi$ V1 to  $\phi$ V2,  $\phi$ H1 to  $\phi$ H2,  $\phi$ H2 to OG.
- 7. Voltage difference between  $\phi V1$ ,  $\phi V2$  gates and LOD/Guard diode.
- 8. Avoid shorting output pins to ground or any low impedance source during operation. Amplifier bandwidth increases at higher currents at the expense of reduced gain (sensitivity). Operation at these values will reduce MTTF.
- 9. Operating and storage temperature. Noise performance will degrade at higher temperatures. Long term storage at these temperatures will accelerate color filter degradation.
- 10. T=25°C. Excessive humidity will degrade MTTF.

#### CAUTION: This device contains limited protection against Electrostatic Discharge (ESD). Devices should be handled in accordance to strict ESD procedures for Class 1 devices.



## **3.2 DC Operating Conditions**

Description	Symbol	Min.	Nom.	Max.	Units	Max DC Current (mA)	Notes
Reset Drain	Vrd	11.3	11.5	11.7	V	0.01	
Output Amplifier Return	Vss	1.0	1.4	1.5	V	0.40	
Output Amplifier Supply	Vdd	14.5	15.0	15.5	V	Iout + Iss	
Substrate	Vsub		0		V	0.01	
Output Gate	OG	4.8	5.0	5.2	V	0.01	
Lateral Drain / Guard Ring	LOD/Guard	9.5	10.0	10.5	V	0.01	
Video Output Current	Iout		-5	-10	mA	-	1

#### Notes:

1. An output load sink must be applied to Vout to activate output amplifier - see Figure below.



Component values may be revised based on operating conditions and other design considerations.

Figure 4 - Recommended Output Structure Load Diagram



#### 3.3 **AC Operating Conditions**

Description	Symbol	Level	Min.	Nom.	Max.	Units	Est. Effective Capacitance	Notes
							Capacitance	
Vertical CCD Clock - Phase 1	φV1	Low	-8.5	-8.2	-8.0	V	139nF	1
		High	0.5	1.0	1.5	V	(total)	
Vertical CCD Clock - Phase 2	<b>φ</b> V2	Low	-8.5	-8.2	-8.0	V	164nF	1
		High	0.5	1.0	1.5	V	(total)	
Horizontal CCD Clock - Phase 1	фН1	Low	-2.8	-2.6	-2.4	V	309pF	1
		High	7.8	8.0	8.2	V		
Horizontal CCD Clock - Phase 2	<b></b> фН2	Low	-2.8	-2.6	-2.4	V	200pF	1
		High	7.8	8.0	8.2	V		
Reset Clock	φR	Low	3.3	3.5	3.7	V	брF	1
		High	10.3	10.5	10.7	V		

Notes:

All pins draw less than 10µA DC current. Capacitance values relative to Vsub. 1.

#### 3.4 **AC Timing Conditions**

Description	Symbol	Min.	Nom.	Max.	Units	Notes
φH1, φH2 Clock Frequency	$f_{\rm H}$		4	10	MHz	1, 2, 6
φV1, φV2 Clock Frequency	$f_V$		50	100	kHz	1, 2, 6
φH1, φH2 Rise / Fall Times		5		10	%	3
φV1, φV2 Rise / Fall Times		5		10	%	3
фH1, фH2 Cross-over		30	50	70	%	4a
φV1, φV2 Cross-over		-3.0	-1.5	0	V	4b
Pixel Period (1 Count)	te	100	250		ns	2
φH1, φH2 Setup Time	tohs	1	5		us	
	t∳R	10	20		ns	5
φV1, φV2 Clock Pulse Width	t∳v	5	10		us	2
фН2 - Video Delay	t <sub>HV</sub>	10	12.5	15	ns	
$\phi R$ - Video Delay	t <sub>RV</sub>	2	2.8	4	ns	
Readout Time	t <sub>readout</sub>	237	587		ms	7
Integration Time	t <sub>int</sub>		Note 6			7
Line Time	t <sub>line</sub>	195	482.5		us	8
Flush Time	t <sub>flush</sub>	12.3	24.8		ms	9

#### Notes:

- 1.
- 50% duty cycle values. CTE will degrade above the nominal frequency. 2.
- 3. Relative to the clock period (based on 10/90% of
- high/low levels). 4a. Relative to clock amplitude.
- 4b. Relative to ground.

- $\varphi R$  should be clocked continuously. Integration time is user specified. 5. 6.
- 7. Longer times will degrade noise performance.
- 8. First line out of each frame requires additional  $t_{\phi V}$ .
- 9. Flush time stated represents 1216 line cycles.





Figure 5 - Timing Diagrams



## 4.1 Performance Specifications

All values measured at  $25^{\circ}$ C, 4MHz data rates, tint = 250msec, treadout = 587msec, nominal operating conditions and using the recommended output load circuits unless specified otherwise. These parameters exclude defective pixels.

Description	Symbol	Min.	Тур.	Max.	Units	Notes	Sampling
Saturation Signal	Vsat		1900		mV	1a	die
Linear Saturation Signal	LVsat	1000			mV	1a, 1b	die
Red Quantum Efficiency ( $\lambda$ =630nm)	Rr	20	24	30	% QE		
Green Quantum Efficiency ( $\lambda$ =540nm)	Rg	17	19	24	% QE		lot
Blue Quantum Efficiency (λ=440nm)	Rb	10	12	14	% QE		
High Level Photoresponse Non-Linearity	PRNL			1	%	2a	die
Low Level Photoresponse Non-Linearity	LLIN YINT	-3.0	-0.7	3.0	mV	2b	die
Photoresponse Non-Uniformity	PRNU		2.0	3.0	%	3	die
Dark Signal	Vdark		3.0	6.0	mV	4	die
Dark Signal Non-Uniformity	DSNU		0.6	1.5	mV p-p	5	die
Read Noise	N		15		e rms	6	design
Dark Signal Doubling Temperature		5.0	6.3	7.0	°C		design
Linear Dynamic Range	DR	75	80		dB	7	design
Red Hue Shift	R HUE		5	10	%	8	die
Blue Hue Shift	B HUE		5	10	%	8	die
Charge Transfer Efficiency	CTE	0.99995	0.99998			9	die
Antiblooming Margin	Xab	8	100			10	die
Output Amplifier DC Offset	Vodc	10	11.4	12	mV	11	die
Output Amplifier Bandwidth	f <sub>-3dB</sub>	60	75		MHz	12	die
Output Video Feedthrough	V <sub>oft</sub>	100	120	160	mV	13	die
Reset Feedthrough	V <sub>R</sub>		620	900	mV	14	die

#### Notes:

- 1a. Increasing output load currents to improve bandwidth will decrease these values.
- 1b. Maximum signal level achieved while meeting PRNL specification.
- 2a. Worst case deviation between Vsat/2 and Vsat relative to a linear fit applied between Vsat/2 +/- Vsat/8 signal levels (center ¼ of data).
- 2b. Worst case Y-intercept value of a linear fit applied between 100mV +/- 12.5mV signal levels.
- 3. rms deviation w.r.t average response on a per color basis.
- 4. Average non-illuminated signal w.r.t. over clocked horizontal register signal.
- 5. Absolute difference between the maximum and minimum average signal levels of 256 x 256 blocks within the sensor.
- 6. rms deviation of all photoactive pixels measured in the dark including amplifier noise sources.
- 7. 20log(Vsat/N) see Note 7 and note 1b.
- 8. Gradual variations in hue (red w.r.t green pixels and blue w.r.t. green pixels) in regions of interest across the entire imager.
- 9. Measured per transfer at Vsat min.
- 10. Number of times above the Vsat illumination level required to bloom the sensor (across all columns of imager).
- 11. Video level offset w.r.t. ground
- 12. Last stage only. Assumes 10pF off-chip load.
- 13. Amount of artificial signal due to  $\phi$ H2 coupling.
- 14. Amplitude of feedthrough pulse in Vout due to  $\phi R$  coupling.



## 4.2 Typical Performance Characteristics



Figure 6 - Typical Quantum Efficiency Curves (Clear Cover Glass)



Figure 7 – Typical Quantum Efficiency Curves (IR Cover Glass)



## 4.2 Typical Performance Characteristics



Figure 8 - Photoresponse Linearity (Full Scale)



Figure 9 - Photoresponse Linearity (Low Level)



Figure 10 - Photoresponse Linearity (High Level)



## 4.3 Defect Classification

All defect tests performed at T=25°C,  $t_{int} = 250 \text{ ms}$  and  $t_{readout} = 1000 \text{ ms}$ 

## **Total Defects**

Points	Clusters	Columns
Total	Total	Total
<u>&lt; 500</u>	<u>&lt;</u> 20	<u>&lt;</u> 20

Point Defects	A pixel which deviates by more than 5mV above or below neighboring pixeks under non-illuminated or low light level (<50mV) conditions OR A pixel which deviates by more than 7% above or 11% below neighboring pixels under illuminated conditions.
Cluster Defect	A grouping of not more than 5 adjacent point defects.
Column Defect	A grouping of 6 or more point defects along a single column OR A column which deviates by more than 0.5mV above or below neighboring columns under non-illuminated or low light level conditions OR A column which deviates by more than 1.5% above or below neighboring columns under illuminated conditions
	Column defects are separated by no less than 5 good columns in either direction



## 5.1 Quality Assurance and Reliability

- 5.1.1 Quality Strategy: All devices will conform to the specifications stated in this document. This is accomplished through a combination of statistical process control and inspection at key points of the production process.
- 5.1.2 Replacement: All devices are warranted against failure in accordance with the terms of Terms of Sale.
- 5.1.3 Cleanliness: Devices are shipped free of contamination, scratches, etc. that would cause a visible defect.
- 5.1.4 ESD Precautions: Devices are shipped in a static-safe container and should only be handled at static-safe work stations.
- 5.1.5 Reliability: Information concerning the quality assurance and reliability testing procedures and results are available from the Microelectronics Technology Division and can be supplied upon request.
- 5.1.6 Test Data Retention: Devices have an identifying number of traceable to a test data file. Test data is kept for a period of 2 years after date of shipment.

### 5.2 Ordering Information

See Appendix A for available part numbers

Address all inquiries and purchase orders to:

Microelectronic Technology Division Eastman Kodak Company Rochester, New York 14650-2010 Phone: (716) 722-4385 Fax: (716) 477-4947 E-mail: ccd@kodak.com

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#### WARNING: LIFE SUPPORT APPLICATIONS POLICY

Kodak image sensors are not authorized for and should not be used within Life Support Systems without the specific written consent of the Eastman Kodak Company. Product warranty is limited to replacement of defective components and does not cover injury or property or other consequential damages.



## Appendix

## **Appendix 1 - Part Number Availability**

Note: This appendix may be updated independently of the performance specification. Contact Eastman Kodak for the latest revision

Device	Available	Features
Name	Part Numbers	
KAF-2001CE	2H4020	1732(H) x 1172(V) Full-Frame Color CCD Image Sensor

